

TRANSISTOR(PNP)

FEATURES

- Switching and Linear Amplification
- High Current and Low Voltage
- Complement to PXT2222A

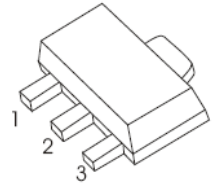
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MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-600	mA
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

SOT-89-3L

1. BASE
2. COLLECTOR
3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}, I_E=0$			-0.01	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.01	μA
DC current gain	h_{FE}	$V_{CE}=-10\text{V}, I_C=-0.1\text{mA}$	75			
		$V_{CE}=-10\text{V}, I_C=-1\text{mA}$	100			
		$V_{CE}=-10\text{V}, I_C=-10\text{mA}$	100			
		$V_{CE}=-10\text{V}, I_C=-150\text{mA}$	100		300	
		$V_{CE}=-10\text{V}, I_C=-500\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1.6	V
		$I_C=-150\text{mA}, I_B=-15\text{mA}$			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-2.6	V
		$I_C=-150\text{mA}, I_B=-15\text{mA}$			-1.3	V
Delay time	t_d	$V_{CC}=-30\text{V}, I_C=-150\text{mA}, I_{B1}=-I_{B2}=-15\text{mA}$			12	ns
Rise time	t_r				30	ns
Storage time	t_s				300	ns
Fall time	t_f				65	ns
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-20\text{mA}, f=100\text{MHz}$	200			MHz